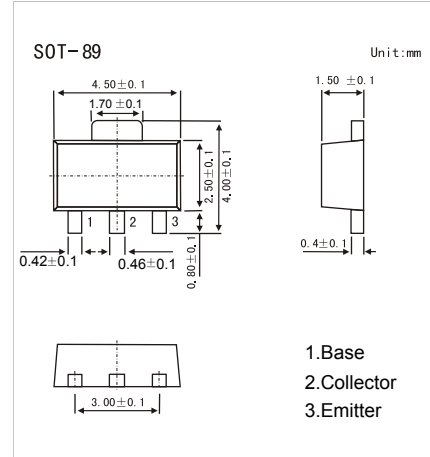


NPN Transistors

KTC4376

■ Features

- 1W (Mounted on Ceramic Substrate)
- Small Flat Package
- Complementary to KTA1664



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	35	V
Collector - Emitter Voltage	V_{CE0}	30	
Emitter - Base Voltage	V_{EB0}	5	
Collector Current - Continuous	I_c	800	mA
Base Current	I_B	160	
Collector Power Dissipation	P_c	500	mW
		1	W
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CB0}	$I_c = 100\mu\text{A}, I_E = 0$	35			V
Collector- emitter breakdown voltage	V_{CE0}	$I_c = 10\text{mA}, I_B = 0$	30			
Emitter - base breakdown voltage	V_{EB0}	$I_E = 100\mu\text{A}, I_c = 0$	5			
Collector-base cut-off current	I_{CBO}	$V_{CB} = 35\text{V}, I_E = 0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 5\text{V}, I_c = 0$			0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_c = 500\text{mA}, I_B = 20\text{mA}$			0.5	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_c = 500\text{mA}, I_B = 20\text{mA}$			1.2	
Base - emitter voltage	V_{BE}	$V_{CE} = 1\text{V}, I_c = 10\text{mA}$	0.5		0.8	
DC current gain	h_{FE}	$V_{CE} = 1\text{V}, I_c = 100\text{mA}$	100		320	
		$V_{CE} = 1\text{V}, I_c = 700\text{mA}$	35			
Collector output capacitance	C_{ob}	$V_{CB} = 10\text{V}, I_E = 0, f = 1\text{MHz}$		13		pF
Transition frequency	f_T	$V_{CE} = 5\text{V}, I_c = 10\text{mA}$		120		MHz

■ Classification of $h_{fe}(1)$

Type	KTC4376-O	KTC4376-Y
Range	100-200	160-320
Marking	PO	PY



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NPN Transistors

KTC4376

Typical Characteristics

